

DESCRIPTION

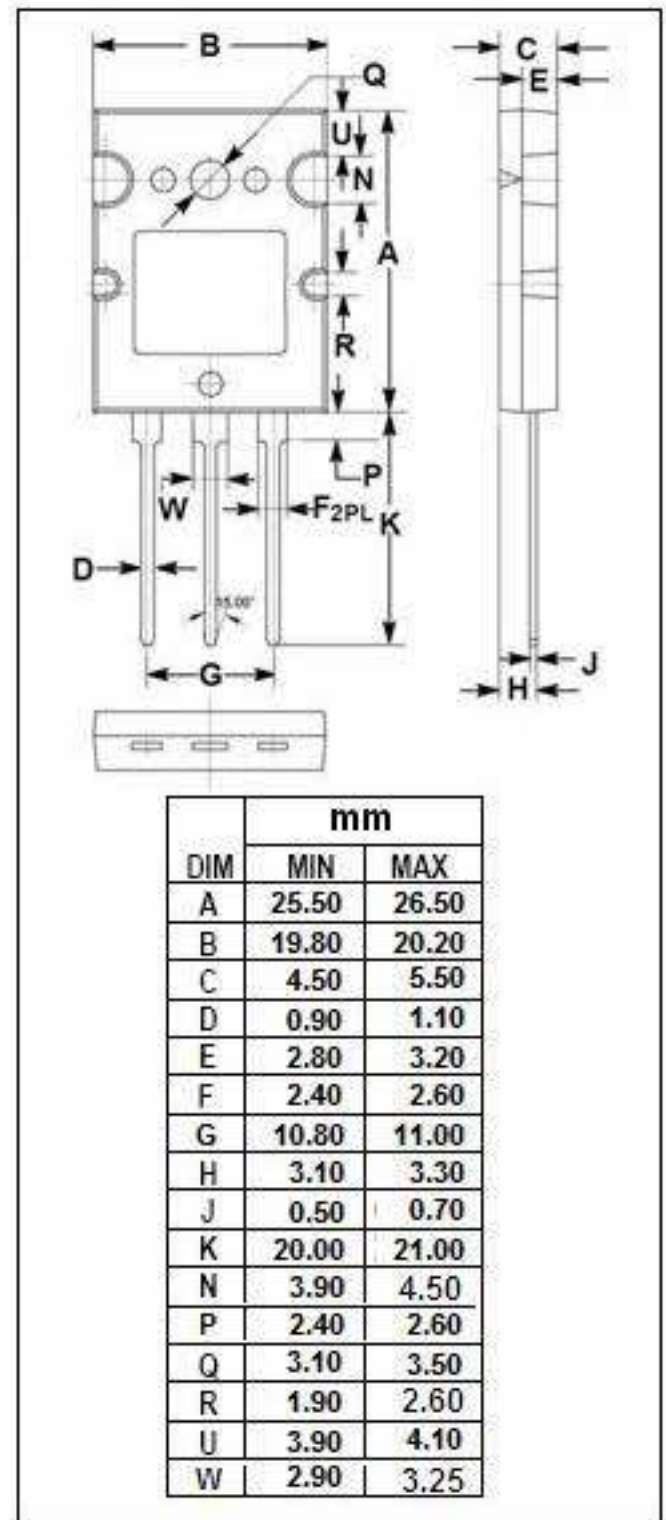
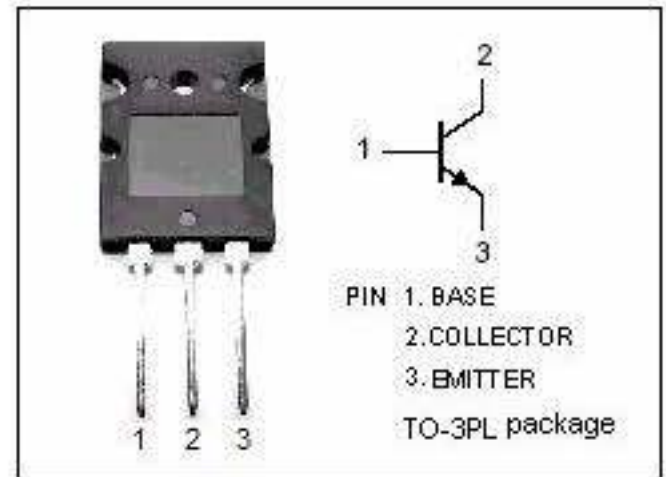
- High Switching Speed
- High Breakdown Voltage-
: $V_{(BR)CBO} = 1500V(\text{Min})$

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	1500	V
V _{CE0}	Collector-Emitter Voltage	800	V
V _{EB0}	Emitter-Base Voltage	6	V
I _C	Collector Current-Continuous	25	A
I _{CM}	Collector Current-Pulse	50	A
P _C	Collector Power Dissipation @ T _C =25°C	250	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



SPTECH Product Specification

SPTECH Silicon NPN Power Transistor

2SC5047

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 10mA; I _B = 0	800			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 20A; I _B =5A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 20A; I _B =5A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μA
I _{CES}	Collector Cutoff Current	V _{CE} = 1500V; R _{BE} = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	8		30	
h _{FE-2}	DC Current Gain	I _C = 20A; V _{CE} = 5V	4		8	
t _{stg}	Storage Time				3.0	μs
t _f	Fall Time	I _C = 12A; I _{B1} =2.4A; I _{B2} = -4.8A			0.2	μs